

PBSS4240Z

40 V, 2 A NPN low VCEsat (BISS) transistor 16 October 2014

Product data sheet

General description 1.

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5240Z

2. **Features and benefits**

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	40	V
Ic	collector current		-	-	2	Α
I _{CM}	peak collector current	$t_p \le 1$ ms; single pulse	-	-	3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	275	mΩ



40 V, 2 A NPN low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1—
3	E	emitter		. M
4	С	collector	☐1 ☐2 ☐3 SC-73 (SOT223)	3 sym016

6. Ordering information

Table 3. Ordering information

Type number	Package	kage				
	Name	Description	Version			
PBSS4240Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

7. Marking

Table 4. Marking codes

•	
Type number	Marking code
PBSS4240Z	S4240Z

40 V, 2 A NPN low VCEsat (BISS) transistor

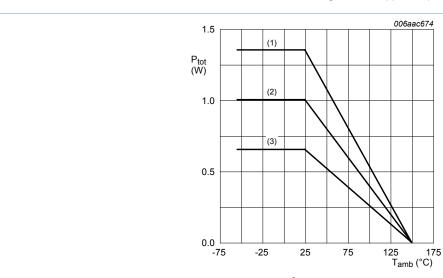
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	40	V
V_{CEO}	collector-emitter voltage	open base		-	40	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	2	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	3	Α
I _B	base current			-	300	mA
I _{BM}	peak base current	t _p ≤ 1 ms; single pulse		-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1	W
			[3]	-	1.35	W
T_j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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40 V, 2 A NPN low VCEsat (BISS) transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance		[1]	-	-	192	K/W
			[2]	-	-	125	K/W
	ambient		[3]	-	-	93	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

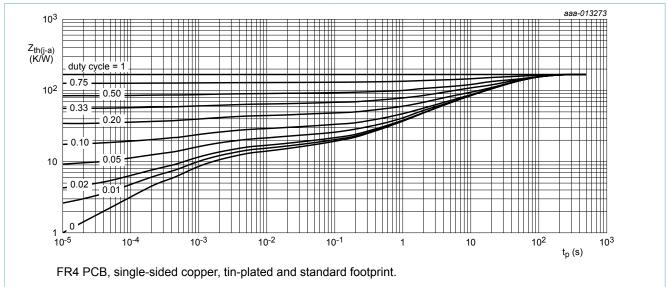
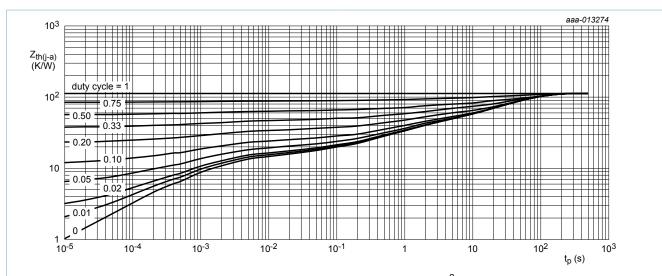


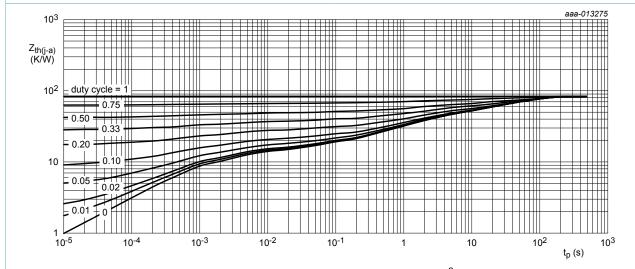
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

40 V, 2 A NPN low VCEsat (BISS) transistor



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

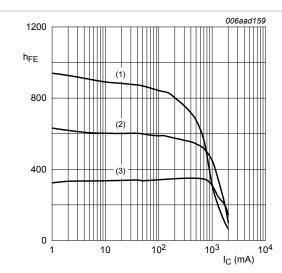
40 V, 2 A NPN low VCEsat (BISS) transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 32 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	$V_{CB} = 32 \text{ V; } I_E = 0 \text{ A; } T_j = 150 \text{ °C}$	-	-	50	μA
ces	collector-emitter cut-off current	V _{CE} = 32 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
ЕВО	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	300	-	-	
		V_{CE} = 5 V; I_{C} = 500 mA; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	300	-	-	
		$V_{CE} = 5 \text{ V; } I_{C} = 1 \text{ A; } t_{p} \le 300 \mu\text{s;}$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	200	-	-	
		V_{CE} = 5 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	75	-	-	
V _{CEsat}	collector-emitter	I _C = 100 mA; I _B = 1 mA; T _{amb} = 25 °C	-	-	80	mV
	saturation voltage	I_{C} = 500 mA; I_{B} = 50 mA; t_{p} ≤ 300 µs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	150	mV
		I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	275	mV
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	550	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	275	mΩ
V_{BEsat}	base-emitter saturation voltage	$I_C = 1 \text{ A}; I_B = 100 \text{ mA}; \text{ pulsed};$ $t_p \le 300 \mu\text{s}; \delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 5 \text{ V; } I_{C} = 1 \text{ A; } t_{p} \le 300 \mu\text{s;}$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	-	-	1.1	V
T	transition frequency	V _{CE} = 10 V; I _C = 50 mA; f = 100 MHz; T _{amb} = 25 °C	150	-	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	10	pF

40 V, 2 A NPN low VCEsat (BISS) transistor



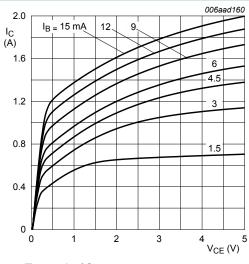
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

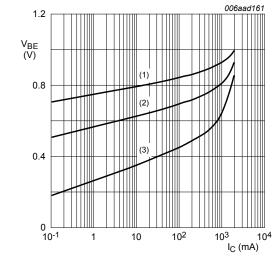
$$(3) T_{amb} = -55 °C$$

Fig. 5. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 6. Collector current as a function of collectoremitter voltage; typical values



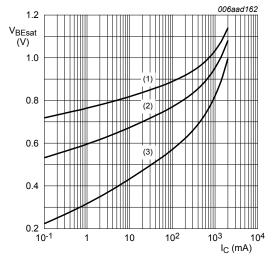
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

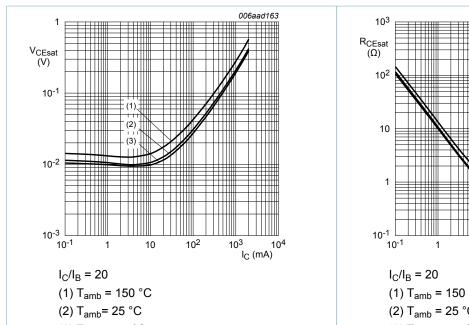
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

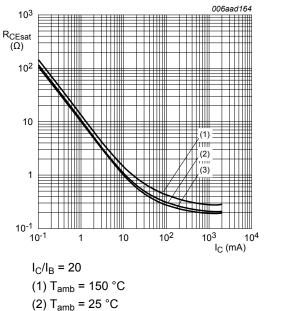
Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

40 V, 2 A NPN low VCEsat (BISS) transistor



(3) T_{amb}= -55 °C

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

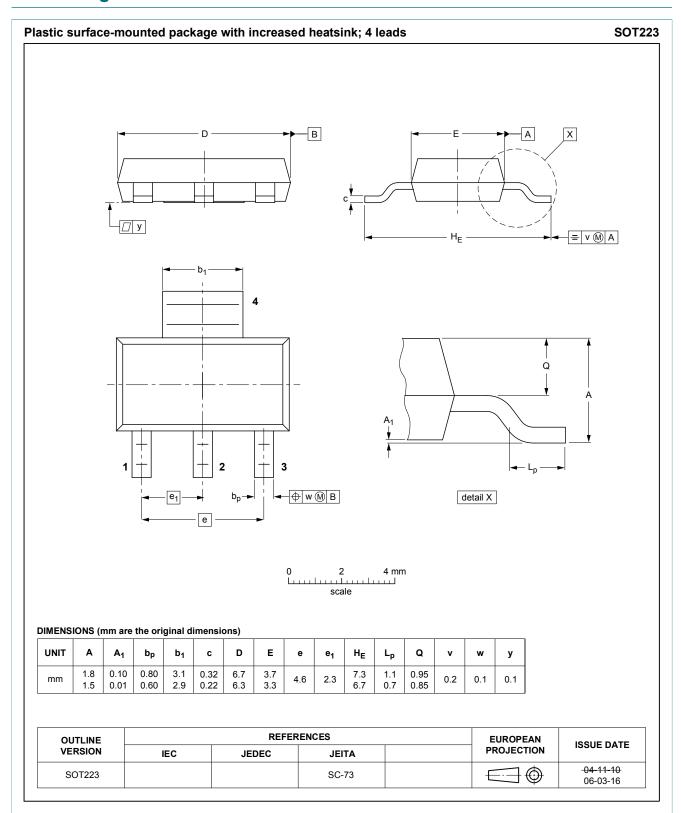
11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

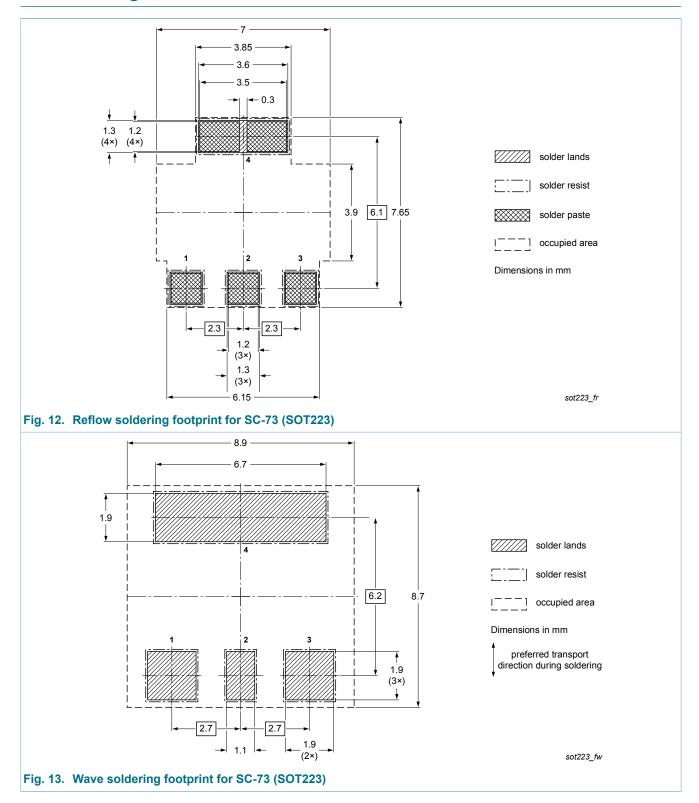
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4240Z v. 1	20141016	Product data sheet	-	-

40 V, 2 A NPN low VCEsat (BISS) transistor

15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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40 V, 2 A NPN low VCEsat (BISS) transistor

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40 V, 2 A NPN low VCEsat (BISS) transistor

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	8
11.1	Quality information	8
12	Package outline	9
13	Soldering	10
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	13

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